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PATENT NUMBER

U.S. UTILITY Patent Application

SUBCLASS

O.I.P.E. 45(2) QA 1 PATENT DATE

APPLICATION NO. CONT/PRIOR 09/596837

438

ART UNIT

EXAMINER Goudrean

Vladimir Vegi -

Method for fabricating microslouctures with deep anisotropic etching of thick silicon wafers

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ORIGI	NAL	CROSS REFERENCE(S)					
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TERMINAL	DRAWINGS			CLAIMS ALLOWED		
DISCLAIMER	Sheets Drwg.	Figs. Drwg.	Print Fig.	Total Claims	Print Claim for O.G.	
☐ The term of this patent			NOTICE OF ALLOWANCE MAILED			
subsequent to (date) has been disclaimed.	(Assistant	Examiner)	(Date)	٠		
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not extend beyond the expiration date of U.S Patent. No.	GEORGE GOUDREAU			ISSUE FEE		
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